A. Interconnect & Package 분과

Room H
하나스퀘어 (B115)

일 시 : 2월 17일(금) 15:30-16:45
세션명 : [FH4-A] 배선용 원자층 증착공정
좌 장 : 김수현(영남대학교), 박진성(단국대학교)

FH4-A-1 15:30-16:00

[Invited]Atomic Layer Deposition of Ru Thin Films with Enhanced Nucleations using Various Ru(0) Metallorganic Precursors and Molecular O2

저자: Soo-Hyun Kim
소속: School of Materials Science and Engineering, Yeungnam University

FH4-A-2 16:00-16:15

Cu 배선 확산방지막용 ALD Ru박막의 계면접착력 평가

저자: 김정규[1], 천태훈[2], 김수현[2], 박영배[1]
소속: [1]안동대학교 신소재공학부 청정에너지 소재기술연구센터, [2]영남대학교 신소재공학부

FH4-A-3 16:15-16:30

Atomic Layer Deposition of Ru and Ru-N Thin Films using N_2/H_2 Plasma as a Reactnat

저자: Ki-Yeung Mun[1], Tae Eun Hong[2], Taehoon Cheon[1], Soo-Hyun Kim[1], Byoung-Yong Lim[3], and Sunjung Kim[3]
소속: [1]School of Materials Science and Engineering, Yeungnam University, [2]Busan Center, Korea Basic Science Institute, [3]School of Materials Science and Engineering, University of Ulsan

FH4-A-4 16:30-16:45

Atomic Layer Deposition of Ru Thin Films using a Novel Ru(0) Metallorganic precursor as a Seed Layer for Copper Metallizations

저자: Seungmin Yeo[1], Sang-Hyeok Choi[1], Taehoon Cheon[1], Soo-Hyun Kim[1], Byoung-Yong Lim[2], and Sunjung Kim[2]
소속: [1]School of Materials Science and Engineering, Yeungnam University, [2]School of Materials Science and Engineering, University of Ulsan